

Development of Machine Learned Interatomic Potentials for Modeling the Effect of Mixed Material Layers on Hydrogen Retention

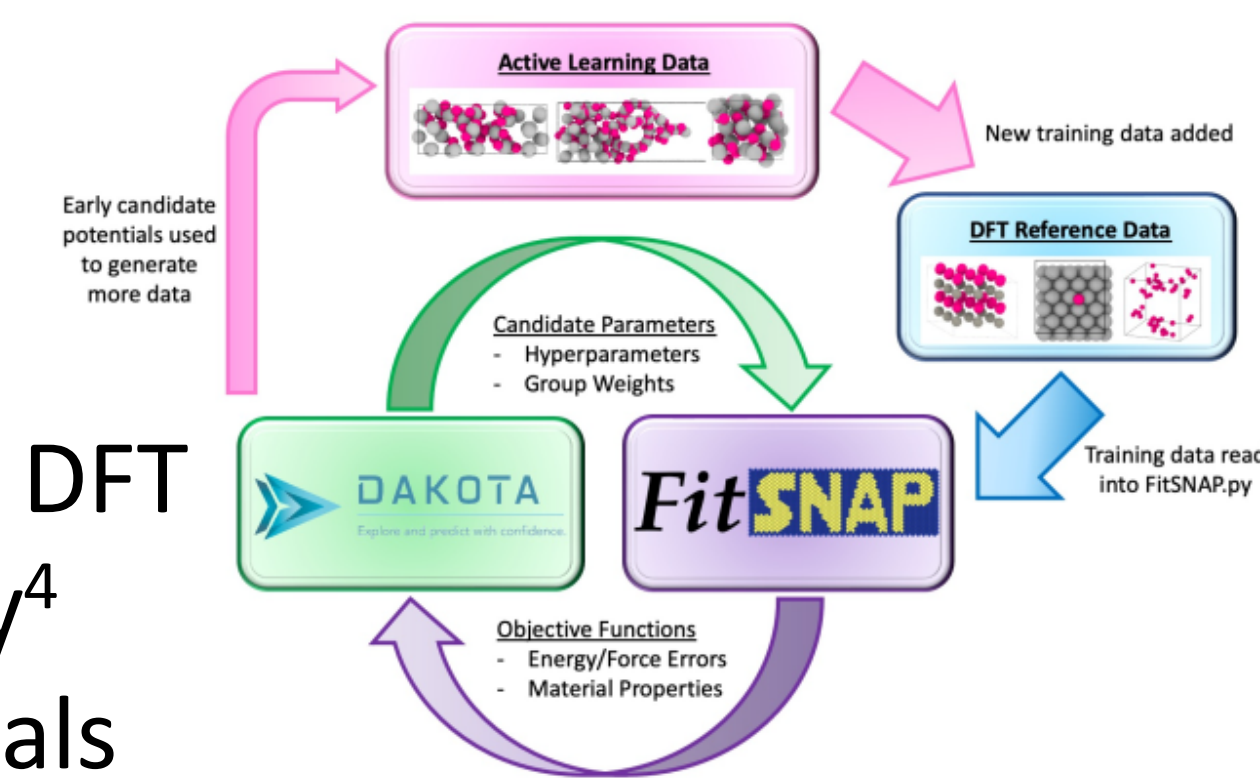
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Motivation

- Divertor component will be subject to high fluxes of mixed ion species including hydrogen, helium, beryllium, and nitrogen
- Hydrogen retention in reactor components is a concern
- Experiments have shown that implantation of other plasma species in the divertor greatly affects H retention¹
- Critical to understand how these mixed materials layers form and their effect on hydrogen diffusion, trapping, and retention

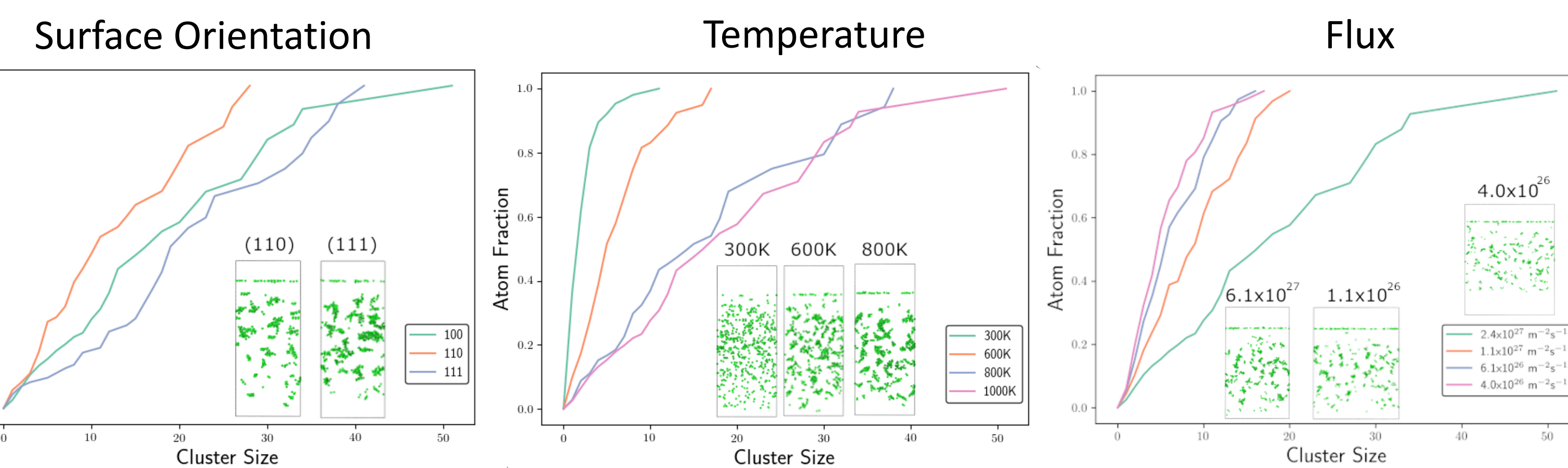
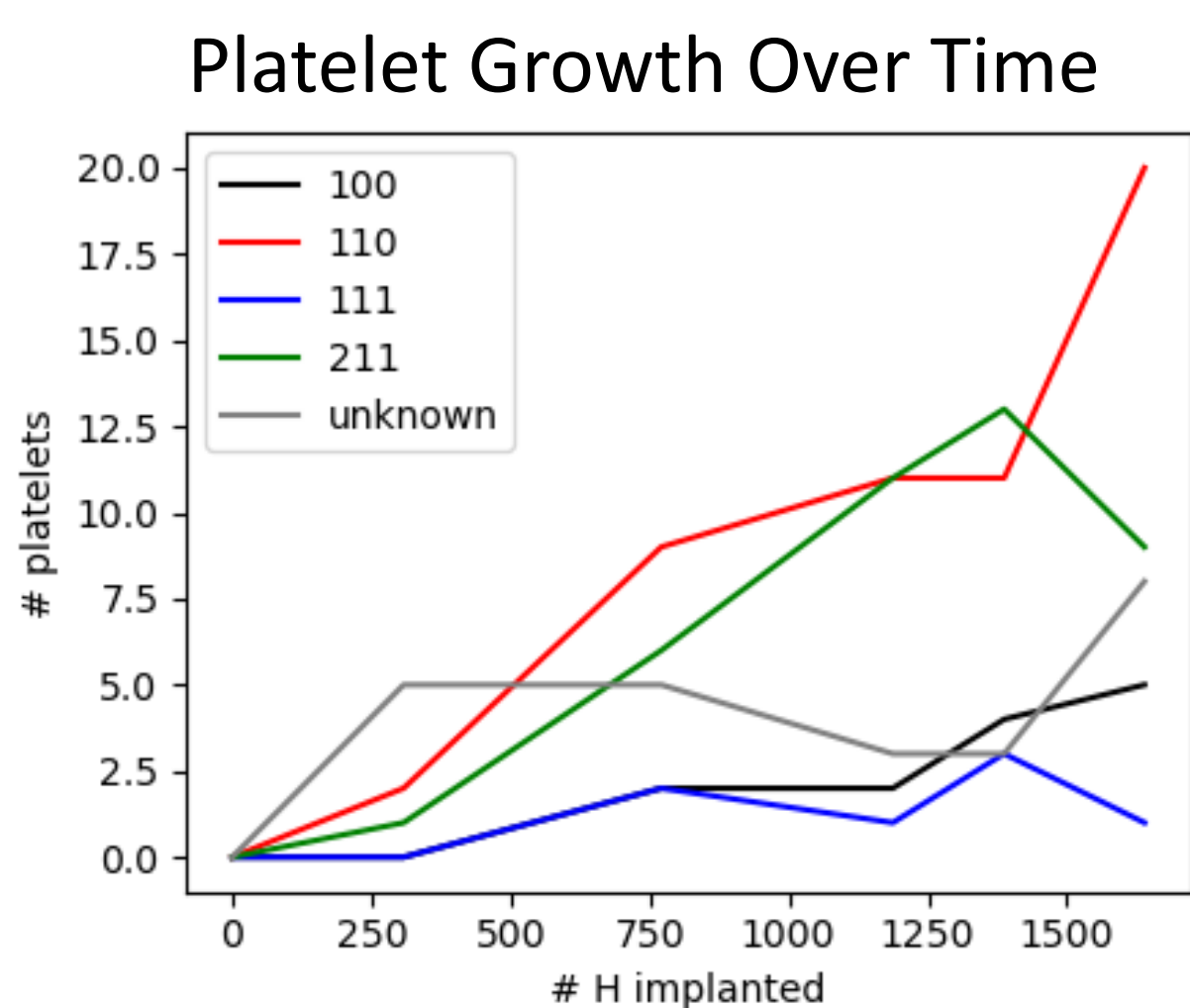
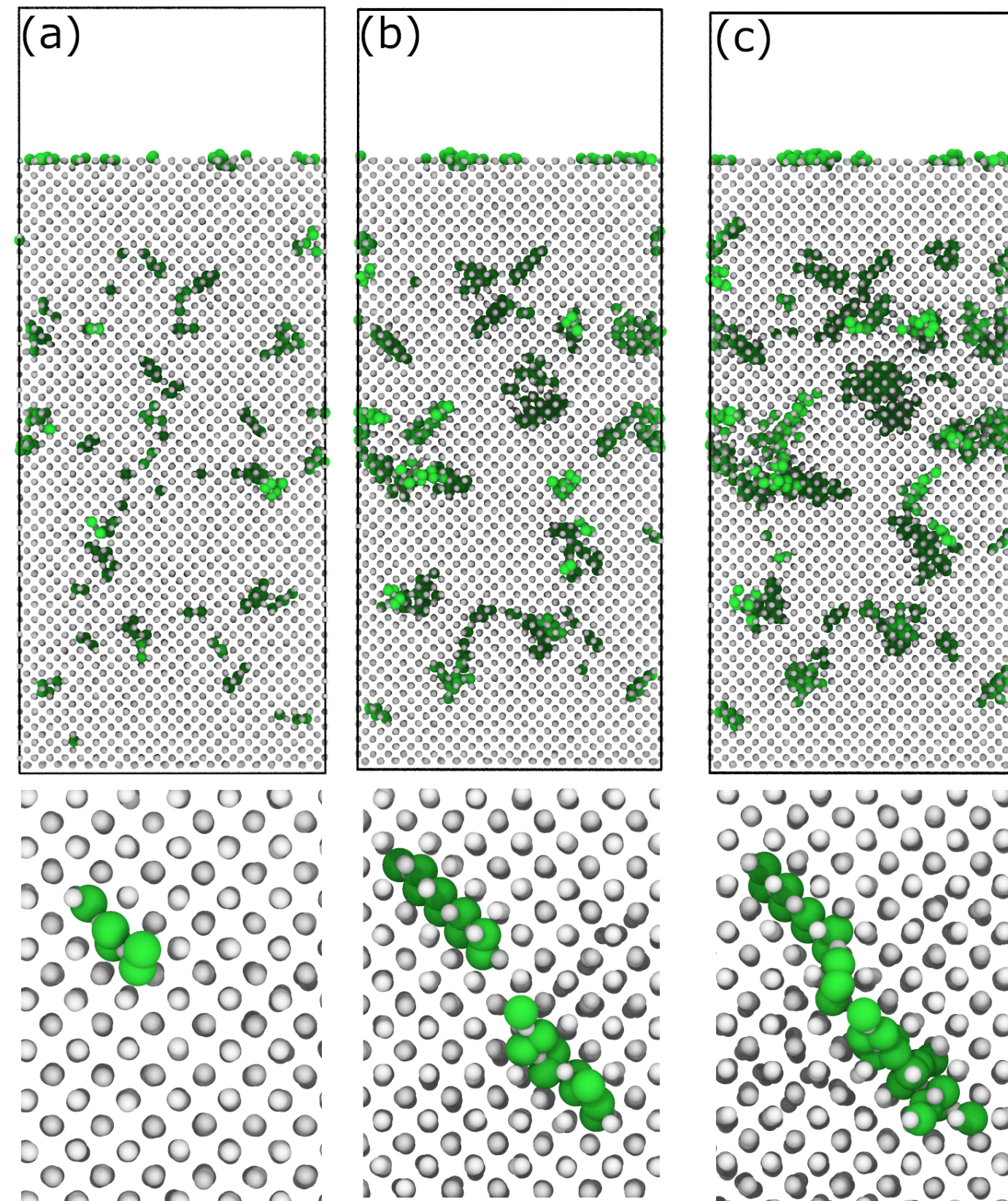
SNAP Potential Development

- Need new potentials that can capture complex chemistry at plasma-material interface
- SNAP^{2,3} is a machine learned interatomic potential trained to DFT data and has improved accuracy⁴ compared to traditional potentials
- Extension of W-Be⁵ SNAP for H and N

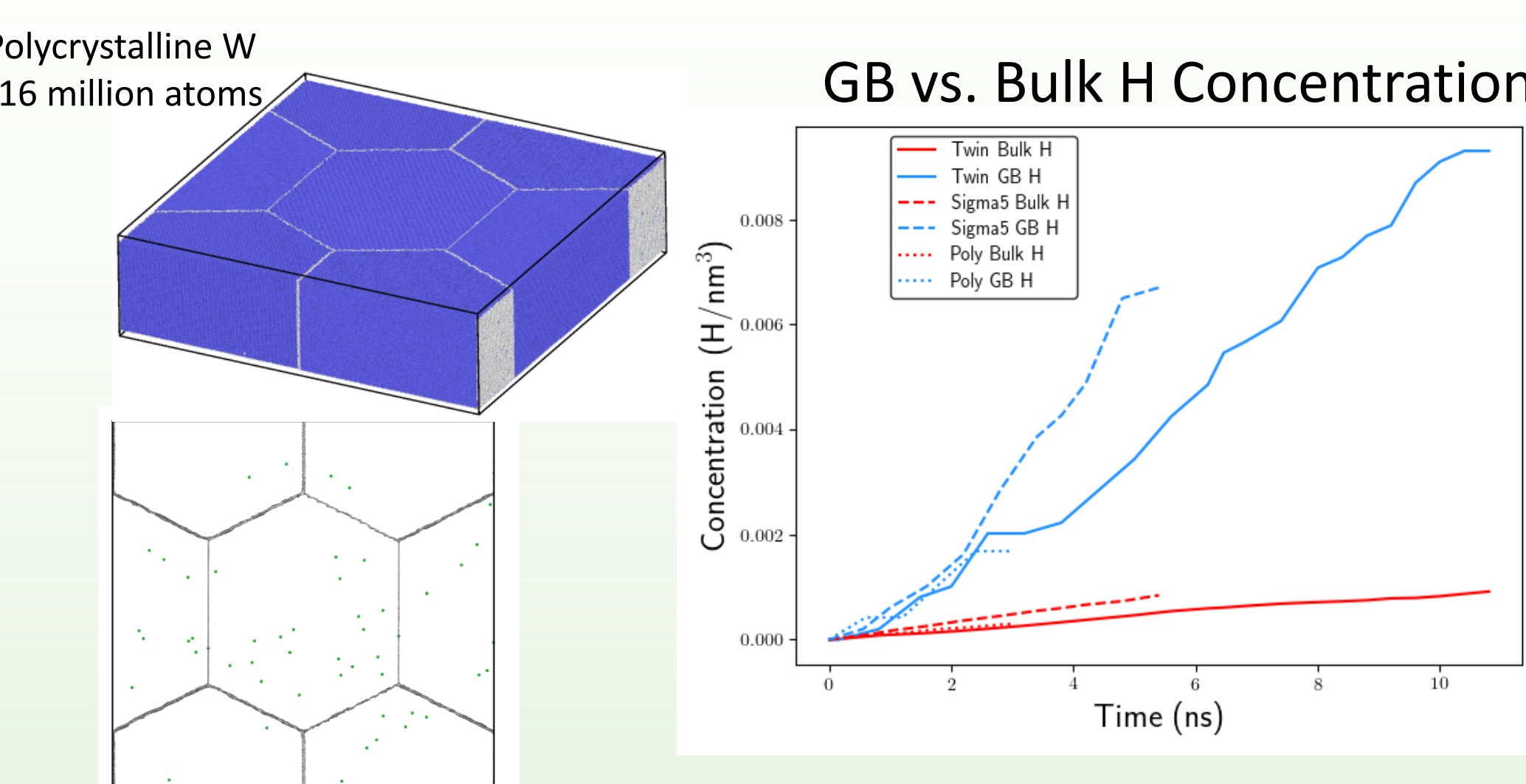


W-H

- 75 eV H implantation into (100) W at 1000 K
- SNAP predicts formation of 2D platelet structures primarily along the (110) direction



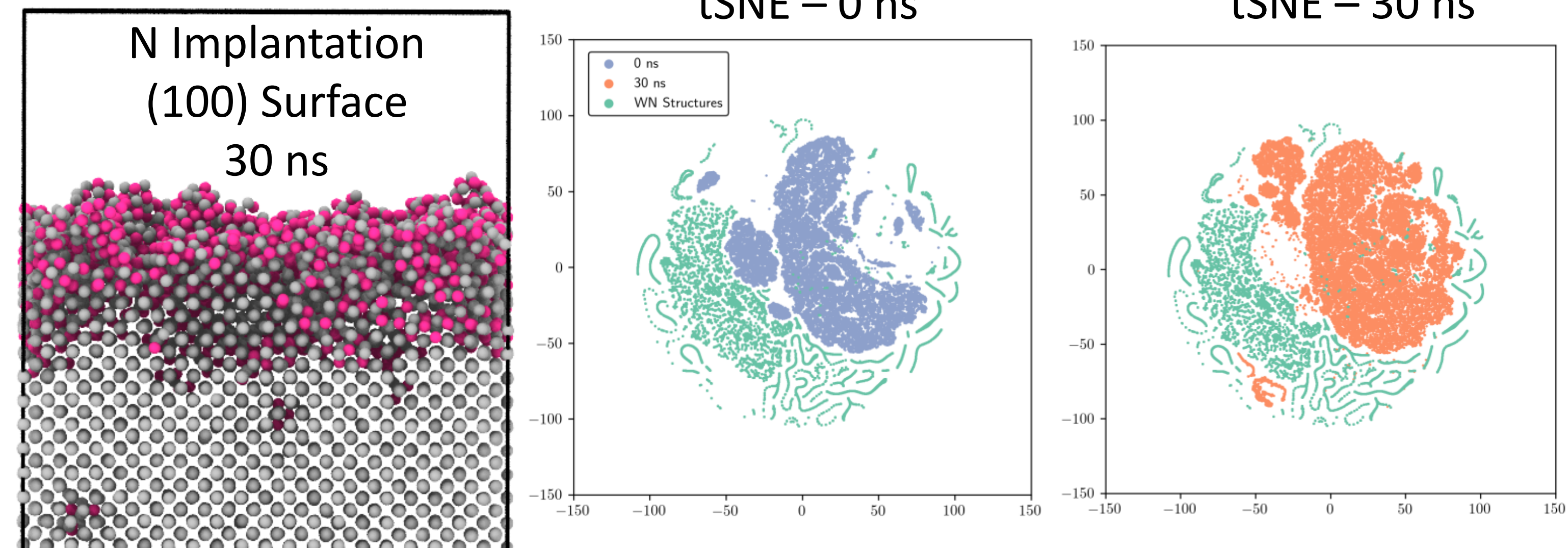
- H platelet growth dependent on temperature on flux
- Requires temperatures higher than 600 K



- Grain boundaries remain a strong trapping site even compared to platelets
- Higher concentrations of H found at GB compared to bulk
- Similar observations at higher H concentrations

W-N

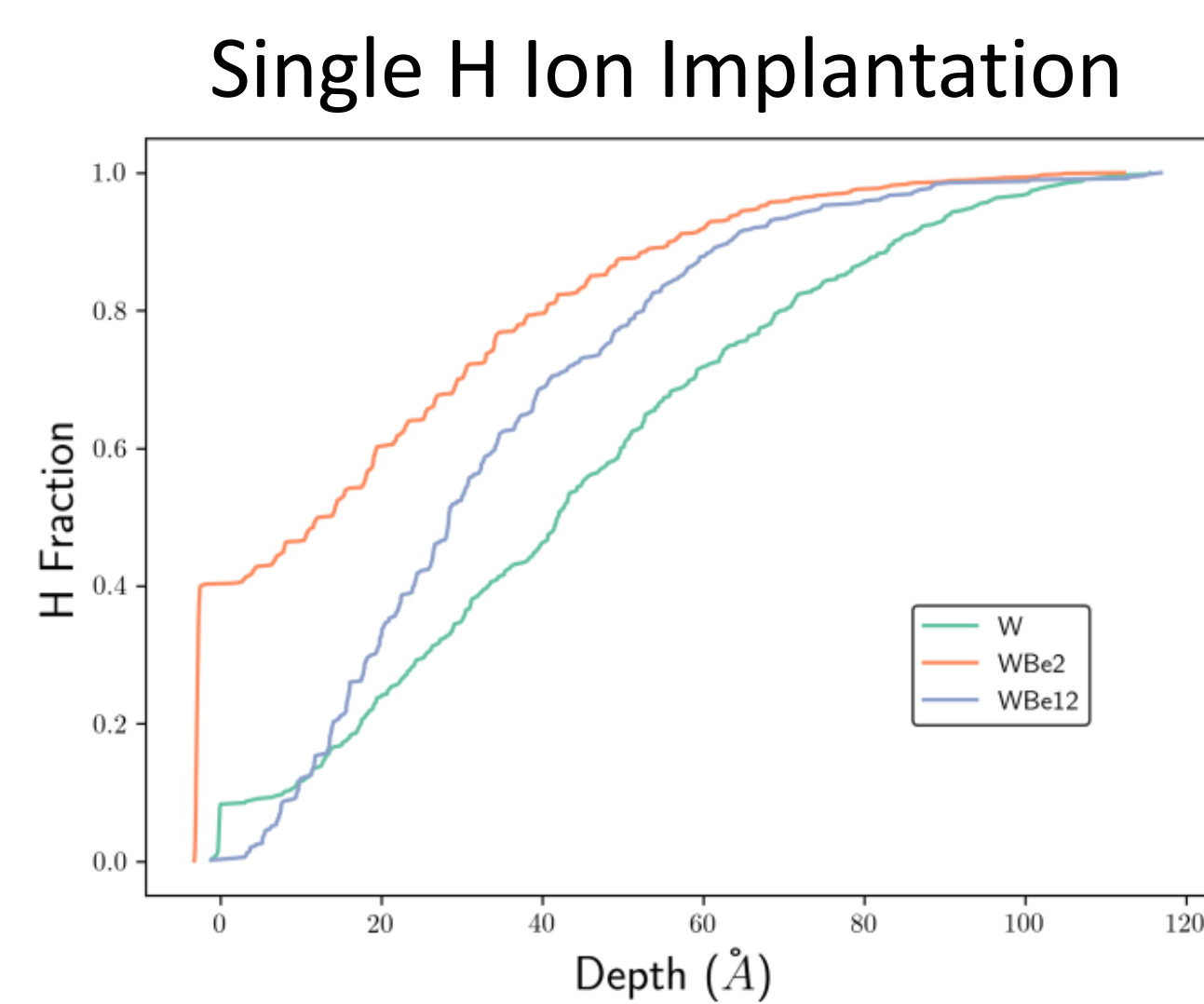
- 75 eV N implantation into (100) W surface at 1000 K
- Nitrogen remains near surface and forms a ~2 nm mixed layer
- tSNE analysis indicates shift in descriptors between 0 ns and 30 ns to more closely align with W-N structures in the training data



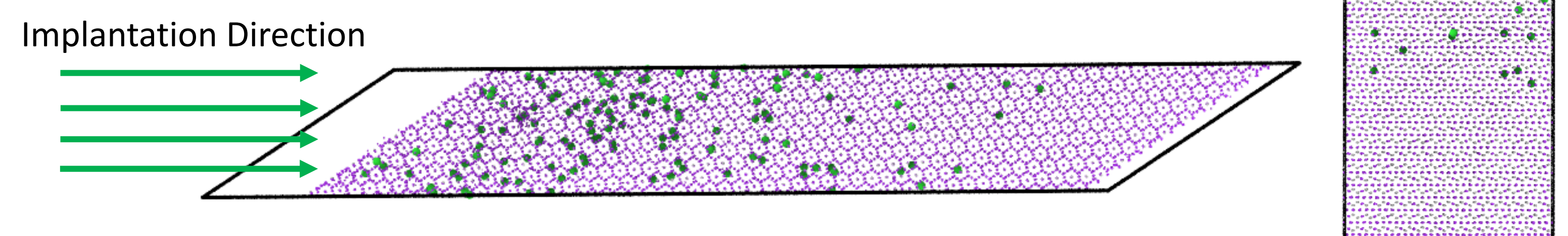
W-Be-H

- Single 60 eV H implantation in WBe₂ and WBe₁₂ at 1000 K indicated high H retention and comparable, but shallower, H depth profiles

	Retention	W Sputt.	Be Sputt.
W - 60 eV	49.3	0	-
WBe ₂ - 60 eV	96.1	0	0.038
WBe ₁₂ - 60 eV	99.1	0	0.017



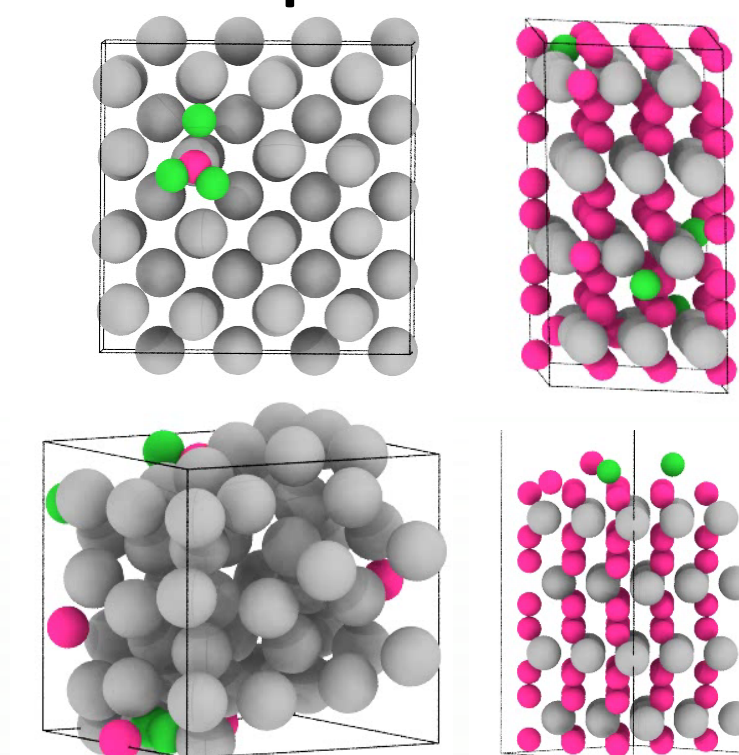
- Cumulative 60 eV H implantation in WBe₂ and WBe₁₂ at 1000 K at 2 ns
- Much less clustering compared to W
- Higher retention in WBe₁₂ (72%) compared to W (51%) and WBe₂ (54%)



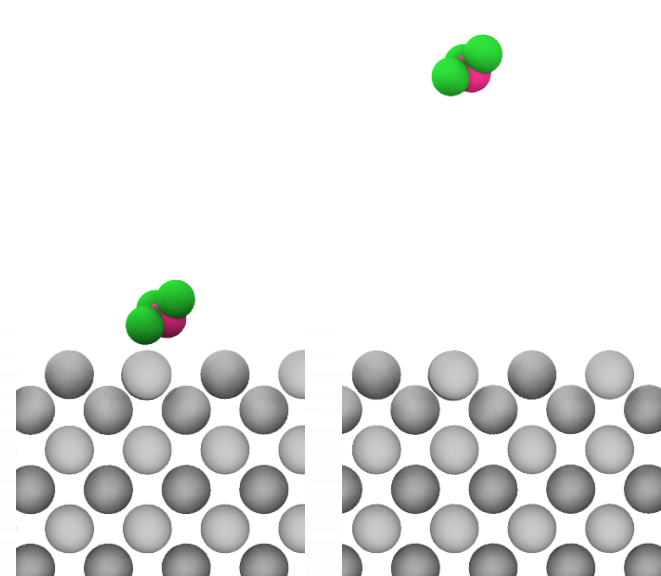
W-H-N

New efforts to develop W-H-N SNAP

Early candidate potentials predict NH_x surface binding energy



Surface Binding Energy	DFT (eV)	SNAP (eV)
NH ₃	-1.05	-0.53
NH ₂	-4.39	-1.44
NH	-6.6	-5.87



Conclusions

- Development of SNAP ML-IAPs for W, Be, H, and N
- SNAP predicts formation of H platelets after implantation
- N implantation results in a mixed materials layer that has structural similarities to tungsten nitrides
- W-Be intermetallics at the surface result in higher H retention particularly for WBe₁₂